

Notice of References Cited	Application/Control No. 10/698,401	Applicant(s)/Patent Under Reexamination CHEN, SHI-MING	
	Examiner B. William Baumeister	Art Unit 2815	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5,877,558	03-1999	Nakamura et al.	257/749
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	JP 9-167857	06-1997	Japan	Fujimoto et al.	H01L 33/00
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Stringfellow et al., "High Brightness Light Emitting Diodes," Semiconductors and Semimetals, 1997, Vol. 48, pages 195-199.
	V	Schnitzer et al., "Ultrahigh spontaneous emission quantum efficiency, 99.7% internally and 72% externally, from AlGaAs/GaAs/AlGaAs double heterostructures," Appl. Phys. Lett. 62 (2), 11 January 1993, pp. 131-133.
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.